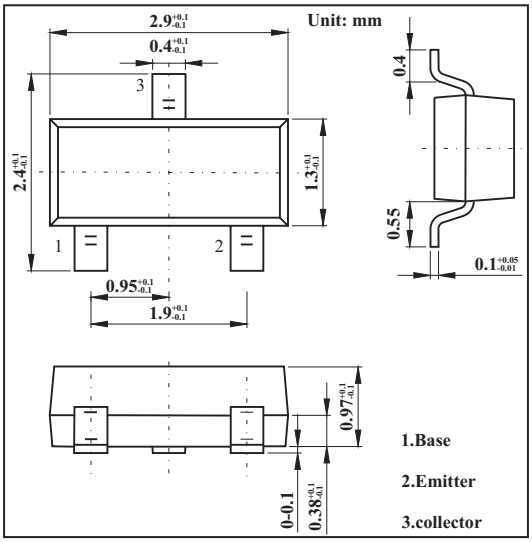
SOT-23 Plastic-Encapsulate Transistors

FEATURES

- Very Low VCE(sat).VCE(sat) = -0.1V(Typ)
  IC / I B= 500 mA / 50mA
- High current capacity in compact package
- Medium Power Transistor
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	40	V
Collector-emitter voltage	V_{CEO}	32	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	0.8	A
Collector current *	I_{CP}	1.5	
Collector power dissipation	P_C	200	mW
Junction temperature	Tj	150	℃
Storage temperature	Tstg	-55 to +150	℃

* Single pulse Pw=100ms

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CBO}	I_C=50ì A	40			V
Collector-emitter breakdown voltage	BV_{CEO}	I_C=1mA	32			V
Emitter-base breakdown voltage	BV_{EBO}	I_E=50ì A	5			V
Collector cutoff current	I_{CBO}	V_{CB}=20V			0.5	uA
Emitter cutoff current	I_{EBO}	V_{EB}=4V			0.5	uA
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C/I_B=500mA/50mA		0.1	0.4	V
DC current transfer ratio	h_{FE}	V_{CE}=3V, I_C=100mA	120		390	
Output capacitance	f_T	V_{CE}=5V, I_E= -50mA, f=100MHz		150		MHz
Transition frequency	Cob	V_{CB}=10V, I_E=0A, f=1MHz		15		pF